

isc Silicon PNP Power Transistor

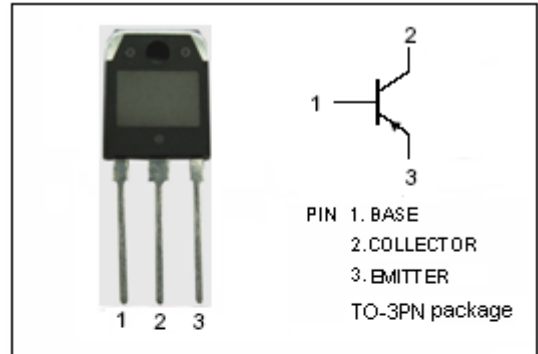
2SB1373

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -160V(\text{Min})$
- Wide Area of Safe Operation
- Complement to Type 2SD2066

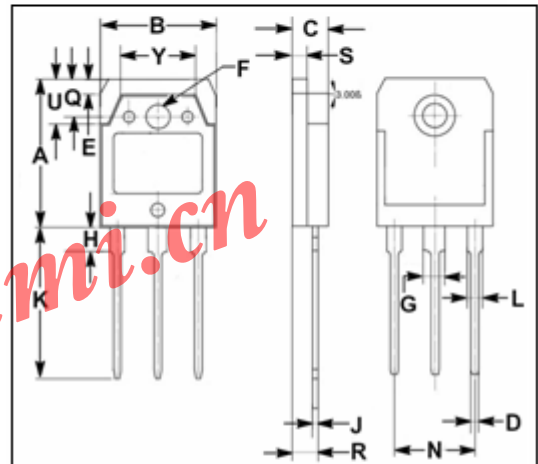
APPLICATIONS

- Designed for high power amplifications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-12	A
I_{CP}	Collector Current-Pulse	-20	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	120	W
	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	2.5	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -8\text{A}; I_B = -0.8\text{A}$			-2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C = -8\text{A}; V_{CE} = -5\text{V}$			-1.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -160\text{V}; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3\text{V}; I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -20\text{mA}; V_{CE} = -5\text{V}$	20			
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	60		200	
h_{FE-3}	DC Current Gain	$I_C = -8\text{A}; V_{CE} = -5\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -5\text{V}; f = 1\text{MHz}$		15		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1\text{MHz}$		400		pF

◆ h_{FE-2} Classifications

Q	S	P
60-120	80-160	100-200